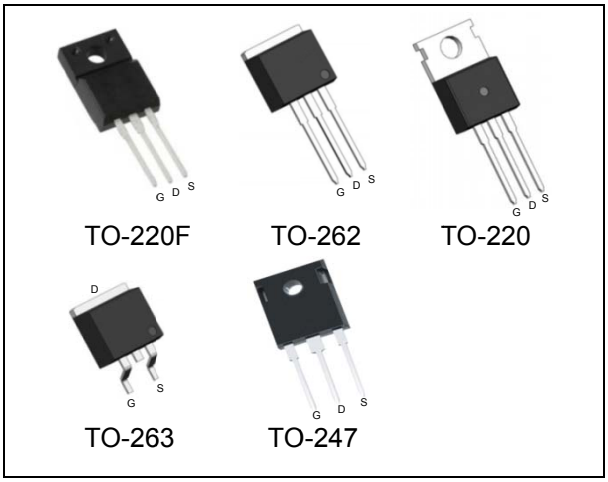
550V 0.087Ω Super Junction Power MOSFET

Description

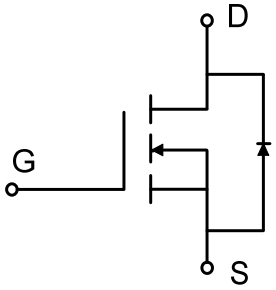
WMOS™ ES is Wayon's new generation super junction MOSFET family that is utilizing charge balance technology for extremely low on-resistance and low gate charge performance. WMOS™ ES is suitable for applications which require superior power density and outstanding efficiency.



Features

- Fast body diode
- Typ. $R_{DS(on)}$ =0.087Ω
- 100% UIS tested
- Pb-free plating, Halogen free

RoHS compliant



Applications

LED Lighting, Charger, Adapter, PC, LCD TV, Server

Absolute Maximum Ratings

Parameter	Symbol	WMK/WMM/WMN/WMJ	WML	Unit
Drain-source voltage	V_{DSS}	550		V
Continuous drain current[1] (T_C = 25°C)	I_D	40		A
(T_C = 100°C)		24		A
Pulsed drain current[2]	I_{DM}	130		A
Gate-source voltage	V_{GS}	±30		V
Avalanche energy, single pulse[3]	E_{AS}	450		mJ
Avalanche energy, repetitive[2]	E_{AR}	0.5		mJ
Avalanche current, repetitive[2]	I_{AR}	3.5		A
Power dissipation (T_C = 25°C)	P_D	210	34	W
- Derate above 25°C		1.68	0.27	W/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to +150		°C
Continuous diode forward current[1]	I_S	40		A
Diode pulse current[2]	$I_{S,pulse}$	130		A

Thermal Characteristics

Parameter	Symbol	WMK/WMM/WMN/WMJ	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	0.6	3.6	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	°C/W

Electrical Characteristics T_c = 25°C, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=0.25 mA	550	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=0.25mA	2.8	3.8	4.8	V
Drain cut-off current	I_{DSS}	V_{DS}=550 V, V_{GS}=0V, T_j = 25°C T_j = 125°C	 - -	 - 80	 10 -	μA
Gate leakage current, forward	I_{GSSF}	V_{GS}=20V, V_{DS}=0V	-	-	100	nA
Gate leakage current, reverse	I_{GSSR}	V_{GS}=-20V, V_{DS}=0V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=6A T_j = 25°C	- -	 0.087	 0.098	 Ω
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS}= 100V, V_{GS}= 0V,	-	1973	-	pF
Output capacitance	C_{oss}	f = 1 MHz	-	102	-	
Reverse transfer capacitance	C_{rss}		-	1.3	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 300V, I_D = 15A	-	43	-	ns
Rise time	t_r	R_G = 25Ω, V_{GS}=10V	-	45	-	
Turn-off delay time	$t_{d(off)}$		-	130	-	
Fall time	t_f		-	25	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DD}=480V, I_D=10A,	-	12	-	nC
Gate to drain charge	Q_{gd}	V_{GS}=0 to 10V	-	14	-	
Gate charge total	Q_g		-	43	-	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=6A	-	-	1.2	V
Reverse recovery time	t_{rr}	V_R=50V, I_F=10A,	-	141	-	ns
Reverse recovery charge	Q_{rr}	dI_F/dt=100A/μs	-	0.96	-	μC
Peak reverse recovery current	I_{rrm}		-	12	-	A

Notes:

1. Limited by $T_{j\,max}$. Maximum duty cycle D=0.5.

2. Pulse width limited by maximum junction temperature.

3. I_{AS} = 3.8 A, V_{DD} = 50V, R_G = 25Ω, starting T_j = 25°C.

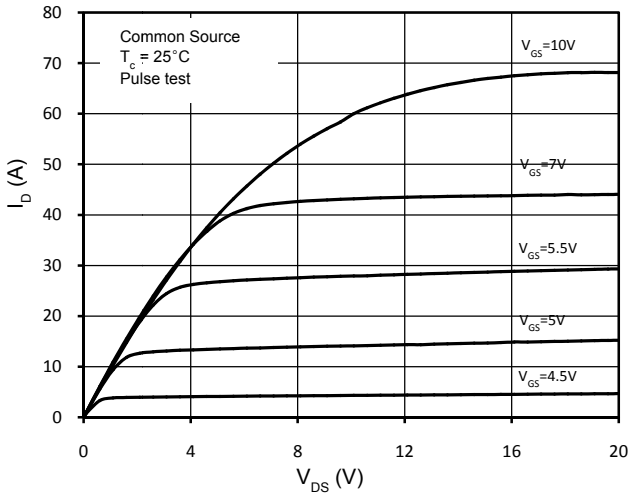


Figure 1.On-Region Characteristics

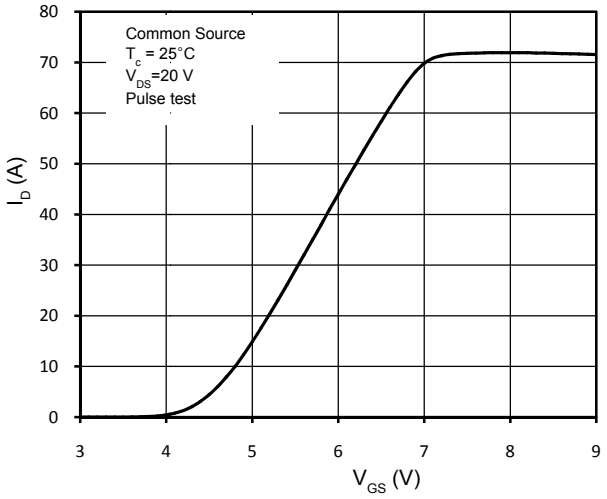


Figure 2. Transfer Characteristics

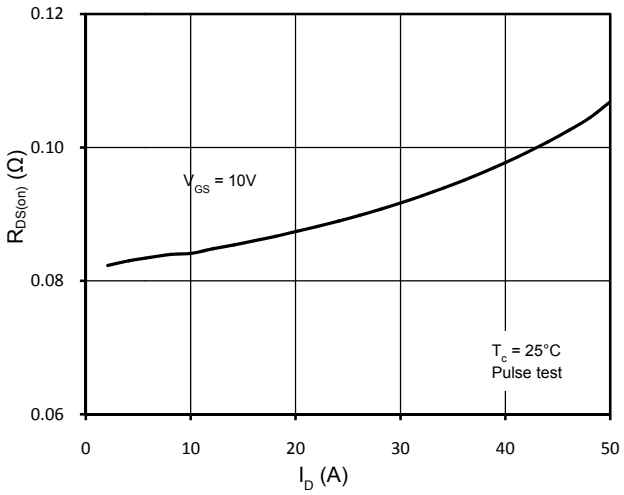


Figure 3. Static Drain-Source On Resistance

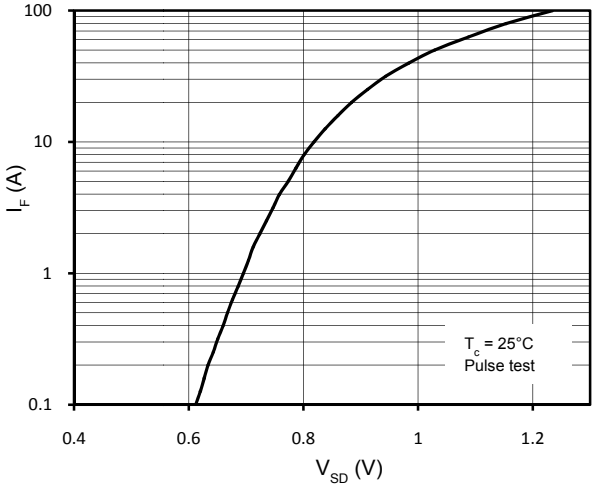


Figure 4. Body- Diode Forward Characteristics

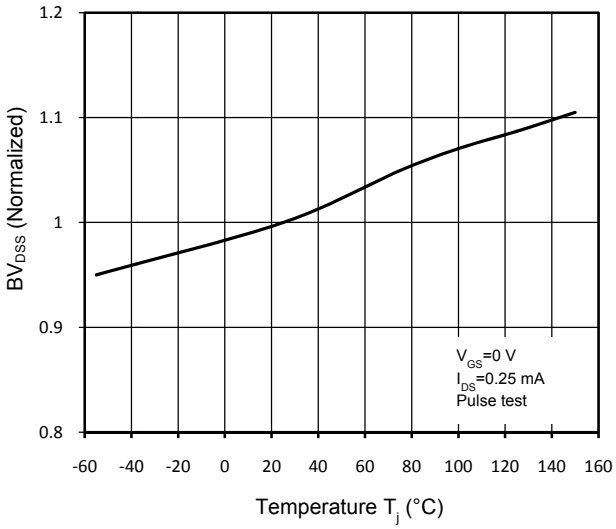


Figure 5. Normalized BV_{DSS} vs. Temperature

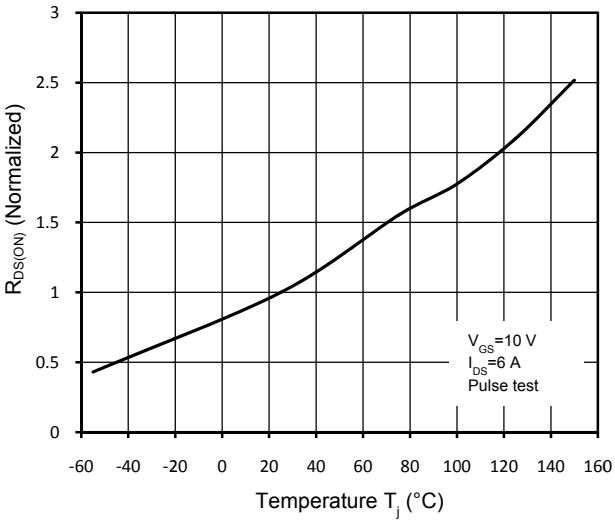


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

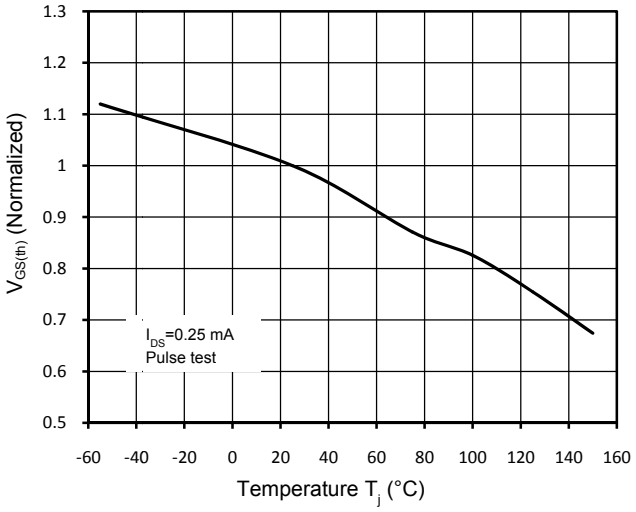


Figure 7. Threshold Voltage vs. Temperature

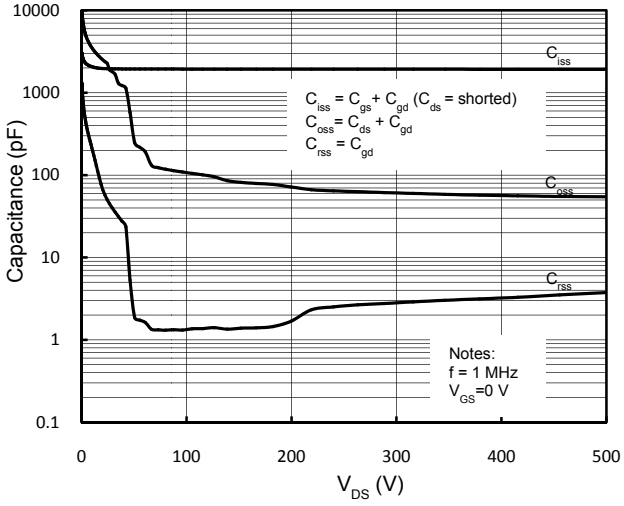


Figure 8. Capacitance Characteristics

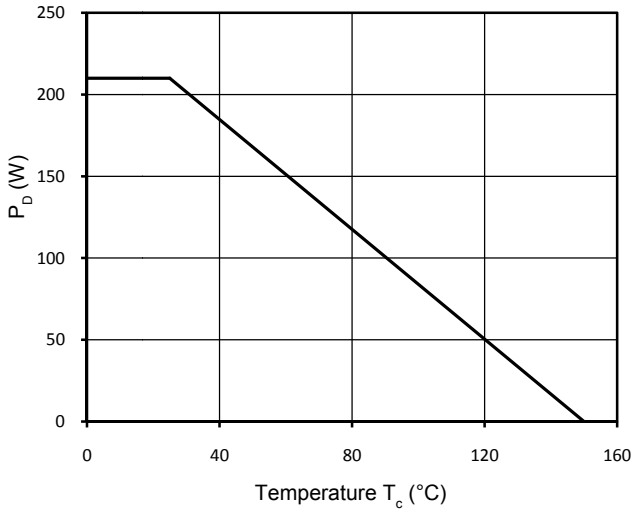


Figure 9. Power Dissipation

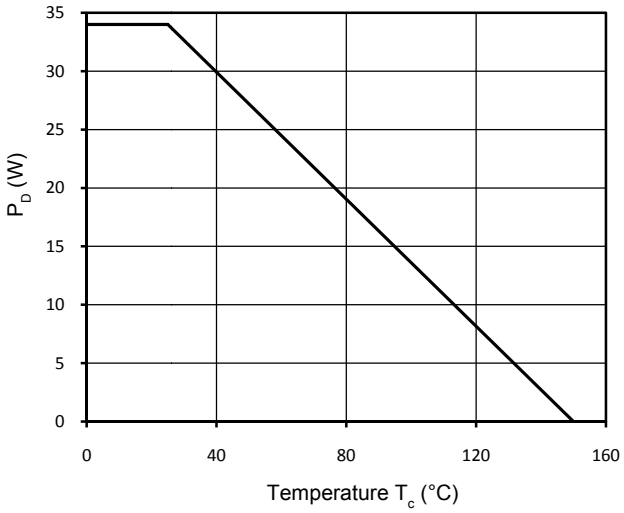


Figure 10. Power Dissipation (TO-220F)

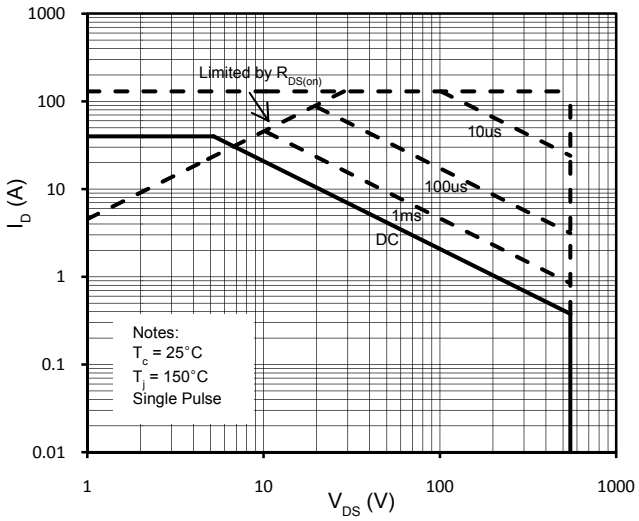


Figure 11. Maximum Safe Operating Area

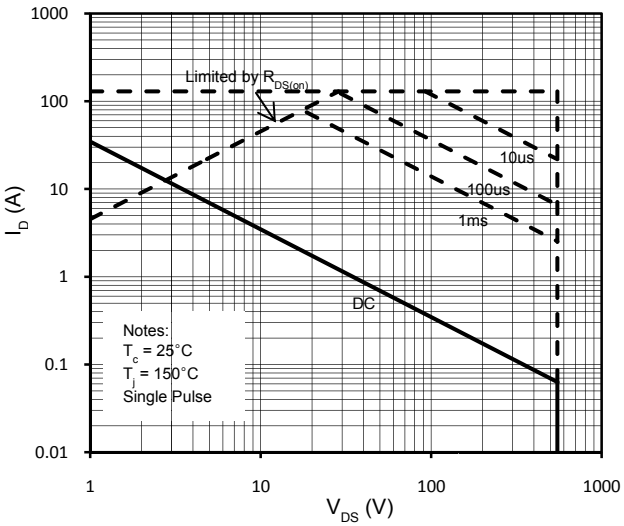


Figure 12. Maximum Safe Operating Area(TO-220F)

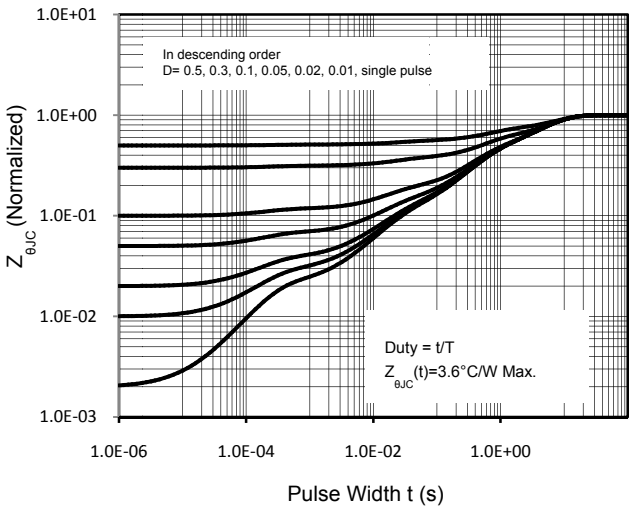


Figure 13. Transient Thermal Response Curve (TO-220F)

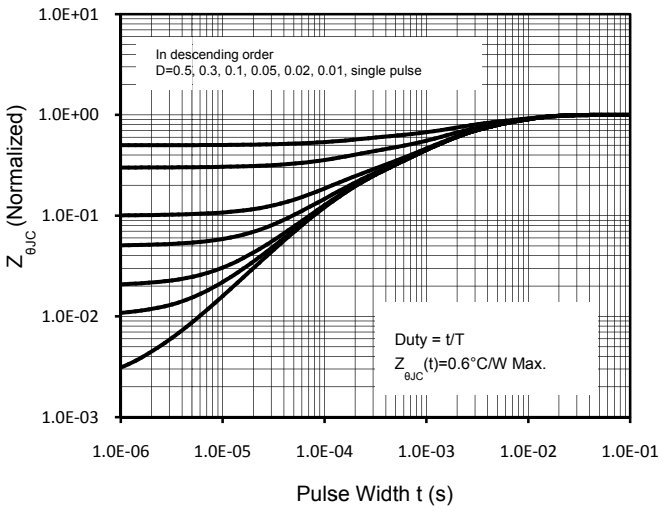


Figure 14. Transient Thermal Response Curve

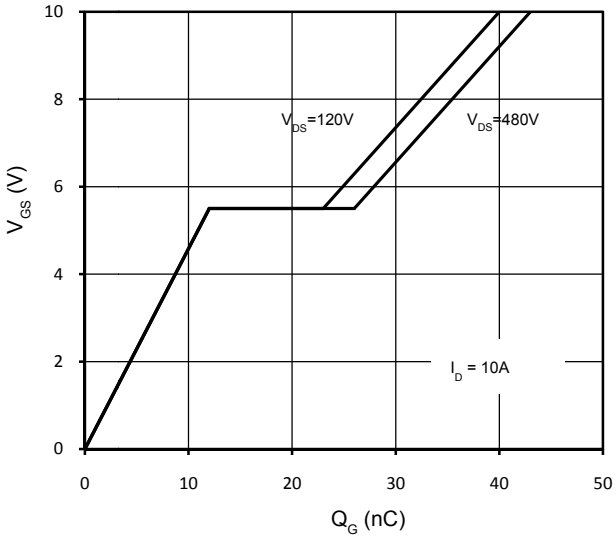
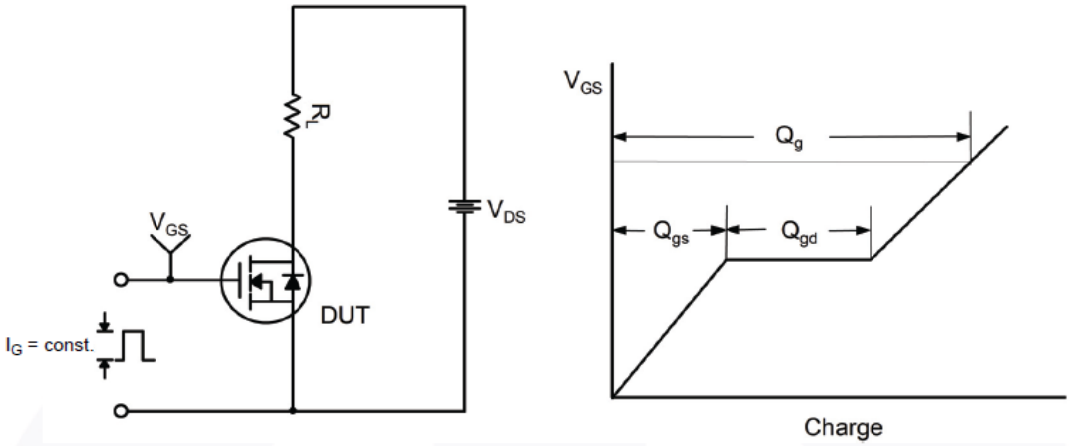
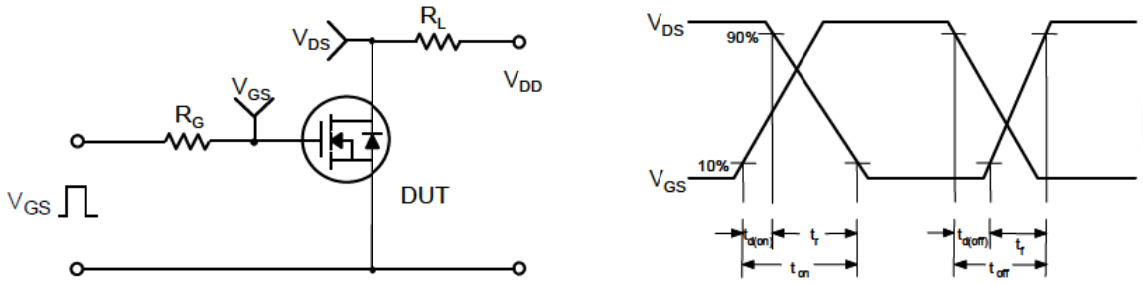


Figure 15. Gate Charge Characteristics

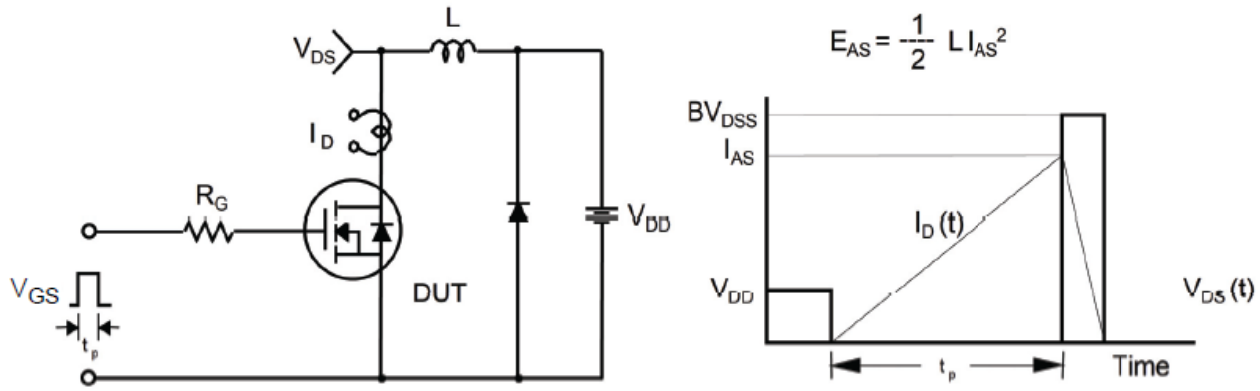
Gate Charge Test Circuit & Waveform



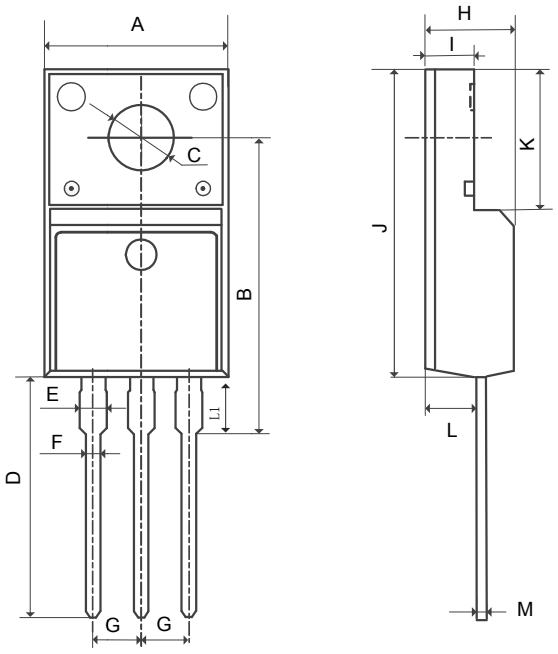
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



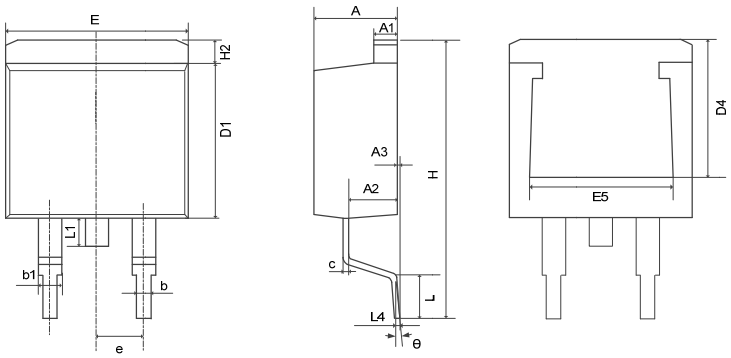
Mechanical Dimensions for TO-220F



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.10	16.10
C	3.03	3.38
D	12.64	13.28
E	1.18	1.58
F	0.70	0.95
G	2.54REF	
H	4.50	4.90
I	2.34	2.74
J	15.57	16.17
K	6.70REF	
L	2.56	2.96
M	0.40	0.65
L1	2.85	3.45

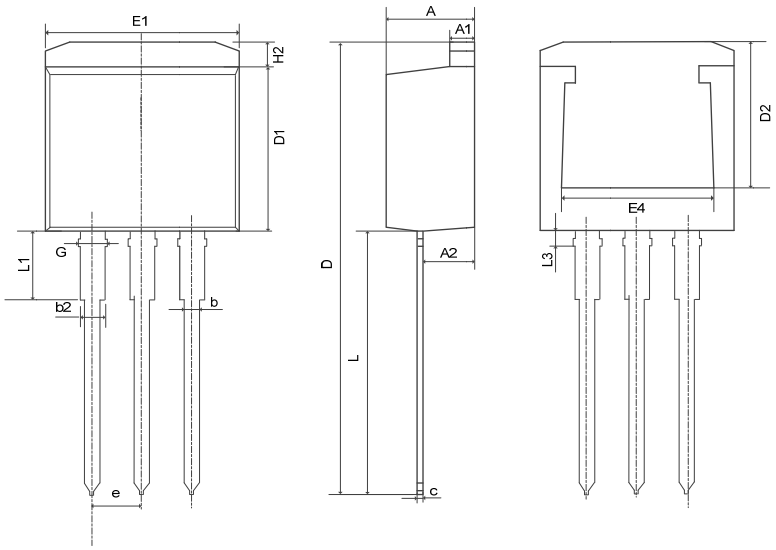
Mechanical Dimensions for TO-263



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.19	2.89
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.60
D1	8.45	9.35
D4	6.60	—
E	9.80	10.40
E5	7.06	—
e	2.54BSC	
H	14.70	16.00
H2	1.07	1.47
L	2.00	2.70
L1	1.15	1.75
L4	0.25BSC	
θ	0°	9°

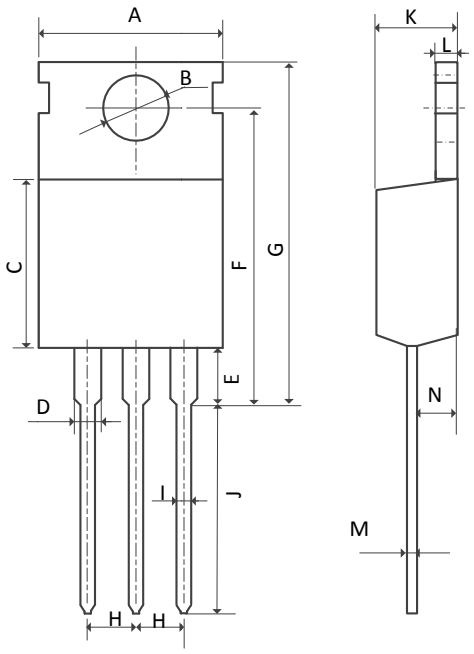
Mechanical Dimensions for TO-262



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.37	4.90
A1	1.17	1.42
A2	2.49	2.89
b	0.71	0.96
b2	1.07	1.47
c	0.28	0.53
D	23.20	24.02
D1	8.45	8.90
D2	6.00	—
E1	9.86	10.40
E4	7.06	—
e	2.54BSC	
G	1.25	1.50
H2	—	1.50
L	13.33	14.16
L1	3.50	4.00
L3	1.28	1.58

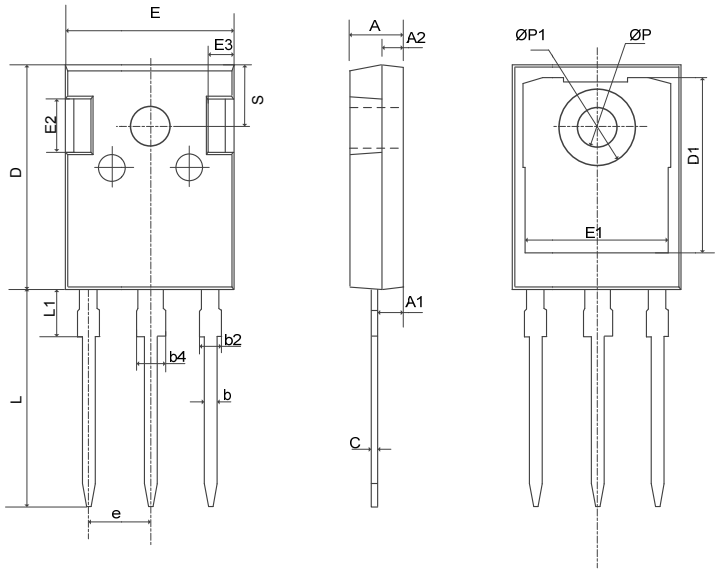
Mechanical Dimensions for TO-220



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.50
F	15.10	16.90
G	19.60MAX	
H	2.54REF	
I	0.70	0.95
J	9.25	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

Mechanical Dimensions for TO-247



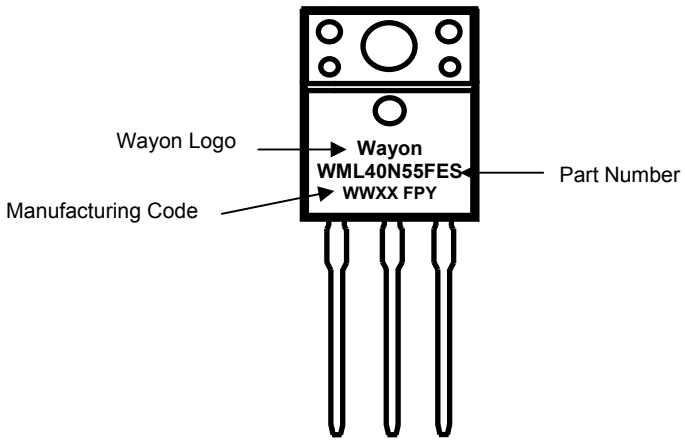
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.80	5.21
A1	2.21	2.61
A2	1.85	2.16
b	1.07	1.36
b2	1.91	2.41
b4	2.87	3.38
c	0.51	0.75
D	20.70	21.30
D1	16.25	17.65
E	15.50	16.13
E1	12.38	13.60
E2	3.68	5.20
E3	1.00	2.70
e	5.44BSC	
L	19.62	20.32
L1	—	4.40
ØP	3.40	3.80
ØP1	—	7.30
S	6.15BSC	

Ordering Information

Part	Package	Marking	Packing method
WML40N55FES	TO-220F	WML40N55FES	Tube
WMK40N55FES	TO-220	WMK40N55FES	Tube
WMN40N55FES	TO-262	WMN40N55FES	Tube
WMM40N55FES	TO-263	WMM40N55FES	Tape and Reel
WMJ40N55FES	TO-247	WMJ40N55FES	Tube

Marking Information



Contact Information

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WAYON website: **http://www.way-on.com**
For additional information, please contact your local Sales Representative.

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